SIEMENS

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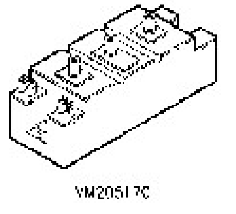
T-23-07

IGBT Module
Preliminary Data

BSM 25 GB 100 D
BSM 25 GAL 100 D

V_{CE} = 1000 V
I_C = 2 x 35 A at T_C = 25 °C
I_C = 2 x 25 A at T_C = 80 °C

- Power module
- Half-bridge/Chopper
- Including fast free-wheel diodes
- Package with insulated metal base plate
- Package outlines/Circuit diagram: 2b, 2c[1]



Half-bridge		Chopper	
Type	**Ordering Code**	**Type**	**Ordering Code**
BSM 25 GB 100 D	C67076-A2101-A2	BSM 25 GAL 100 D	C67076-A2008-A2

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CE}	1000	V
Collector-gate voltage, R_{GE} = 20 kΩ	V_{CGR}	1000	
Gate-emitter voltage	V_{GE}	± 20	
Continuous collector current, T_C = 25 °C T_C = 80 °C	I_C	35 25	A
Pulsed collector current, T_C = 25 °C T_C = 80 °C	$I_{C\,puls}$	70 50	
Operating and storage temperature range	T_j, T_{stg}	- 55 ... + 150	°C
Power dissipation, T_C = 25 °C	P_{tot}	300	W
Thermal resistance, chip-case	R_{thJC}	≤ 0.4	K/W
Insulation test voltage[2], t = 1 min.	V_{is}	2500	V_{ac}
Creepage distance	–	16	mm
Clearance	–	11	
DIN humidity category, DIN 40 040	–	F	–
IEC climatic category, DIN IEC 68-1	–	55/150/56	

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[1] See chapter Package Outline and Circuit Diagrams.
[2] Insulation test voltage between collector and metal base plate referred to standard climate 23/50 in acc. with DIN 50 014, IEC 146, para. 492.1.